





#### 12V PNP LOW SATURATION SWITCHING TRANSISTOR

#### **Features and Benefits**

- BV<sub>CEO</sub> > -12V
- I<sub>C</sub> = -4A Continuous Collector Current
- Low Saturation Voltage (-140mV max @ -1A)
- $R_{SAT} = 60 \text{ m}\Omega$  for a low equivalent On-Resistance
- hFE specified up to -10A for a high current gain hold up
- Low profile 0.6mm high package for thin applications
- R<sub>BJA</sub> efficient, 60% lower than SOT23
- 4mm<sup>2</sup> footprint, 50% smaller than SOT23
- Lead-Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: DFN2020B-3
- Case Material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- Nominal Package Height: 0.6mm
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.01 grams (approximate)

### **Applications**

- MOSFET Gate Driving
- DC-DC Converters
- Charging Circuits
- Power switches
- Motor Control

#### DFN2020B-3



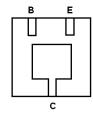
Top View



Bottom View



Device Symbol



Bottom View Pin-Out

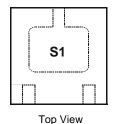
### Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP717MATA	S1	7	8	3000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com
- 3. For Packaging Details, go to our website at http://www.diodes.com.

## **Marking Information**



S1 = Product Type Marking code

ZXTP717MA Document Number DS31881 Rev. 5 - 2 1 of 7





# Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit		
Collector-Base Voltage		V <sub>CBO</sub>	-20			
Collector-Emitter Voltage		V <sub>CEO</sub>	-12	V		
Emitter-Base Voltage		V <sub>EBO</sub>	-7			
Peak Pulse Current		I <sub>CM</sub>	-12			
Continuous Collector Current	(Note 4)	1-	-4			
Continuous Collector Current	(Note 5)	Ic	-4.5			
Base Current		Ι <sub>Β</sub>	-1			

# Thermal Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value U			
Power Dissipation	(Note 4)	0	1.5 12	W mW/°C	
Linear Derating Factor	(Note 5)	P <sub>D</sub>	2.45 19.6		
Thermal Resistance, Junction to Ambient	(Note 4)	D	83		
mermal Resistance, Junction to Ambient	(Note 5)	R <sub>θJA</sub>	51	°C/W	
Thermal Resistance, Junction to Lead	al Resistance, Junction to Lead (Note 6)		16.8		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

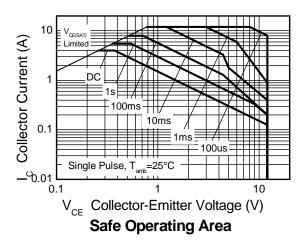
Notes:

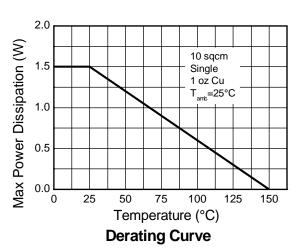
 <sup>4.</sup> For a device surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.
5. Same as note (4), except the device is measured at t ≤ 5 sec.

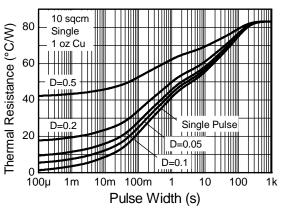
<sup>6.</sup> For a single device, thermal resistance from junction to solder-point (at the end of the drain lead).

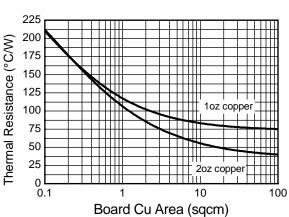


### **Thermal Characteristics**



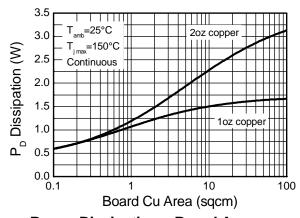






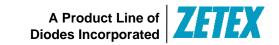
## **Transient Thermal Impedance**

Thermal Resistance v Board Area



Power Dissipation v Board Area





## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

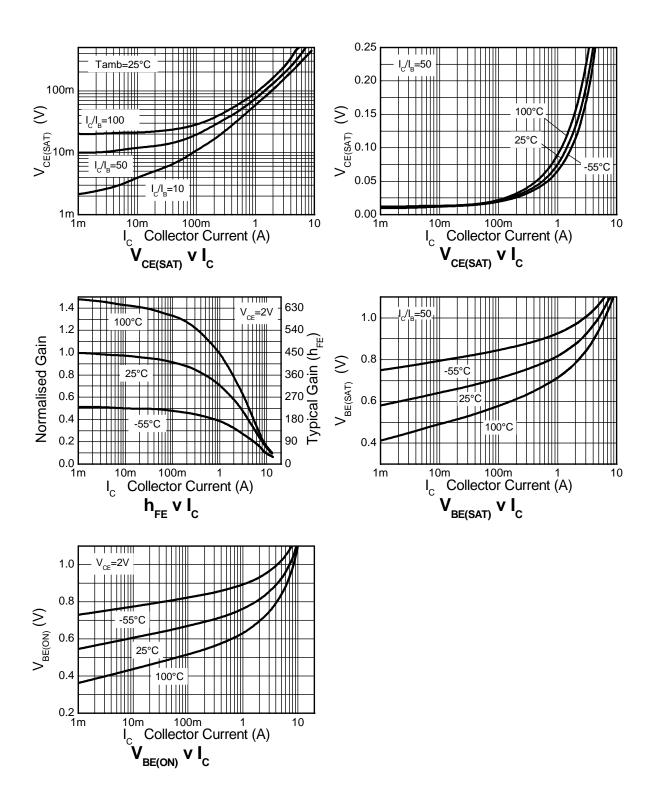
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-20	-35	-	V	I <sub>C</sub> = -100 μA
Collector-Emitter Breakdown Voltage (Note 7)	BV <sub>CEO</sub>	-12	-25	-	V	$I_C = -10 \text{ mA}$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8.5	-	V	I <sub>E</sub> = -100 μA
Collector Cutoff Current	I <sub>CBO</sub>	-	-	-100	nA	V <sub>CB</sub> = -16V
Emitter Cutoff Current	I <sub>EBO</sub>	-	-	-100	. nA	$V_{EB} = -6V$
Collector Emitter Cutoff Current	I <sub>CES</sub>	-	-	-100	nA	V <sub>CES</sub> = -10V
Static Forward Current Transfer Ratio (Note 7)	h <sub>FE</sub>	300 300 180 60 45	475 450 275 100 70	- - - -	-	$\begin{split} &I_{C} = -10 \text{mA}, \ V_{CE} = -2 \text{V} \\ &I_{C} = -100 \text{mA}, \ V_{CE} = -2 \text{V} \\ &I_{C} = -2.5 \text{A}, \ V_{CE} = -2 \text{V} \\ &I_{C} = -8 \text{A}, \ V_{CE} = -2 \text{V} \\ &I_{C} = -10 \text{A}, \ V_{CE} = -2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 7)	V <sub>CE(sat)</sub>	- - - -	-10 -100 -100 -195 -240	-17 -140 -150 -300 -310	mV	$\begin{split} I_C = -0.1A, \ I_B = -10 \text{mA} \\ I_C = -1A, \ I_B = -10 \text{mA} \\ I_C = -1.5A, \ I_B = -50 \text{mA} \\ I_C = -3A, \ I_B = -50 \text{mA} \\ I_C = -4A, \ I_B = -150 \text{mA} \end{split}$
Base-Emitter Turn-On Voltage (Note 7)	$V_{BE(on)}$	-	-0.87	-0.96	V	$I_C = -4A$ , $V_{CE} = -2V$
Base-Emitter Saturation Voltage (Note 7)	$V_{BE(sat)}$	-	-0.97	-1.07	V	$I_C = -4A$ , $I_B = -150mA$
Output Capacitance	$C_obo$	-	21	30	pF	$V_{CB} = -10V. f = 1MHz$
Transition Frequency	f <sub>T</sub>	100	110	-	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz
Turn-On Time	t <sub>on</sub>	-	70	-	ns	V <sub>CC</sub> = -6V, I <sub>C</sub> = -2A
Turn-Off Time	t <sub>off</sub>	-	130	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$

Notes: 7. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu$ s. Duty cycle  $\leq$  2%.

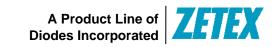




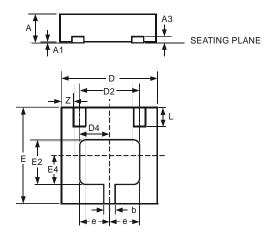
## **Typical Electrical Characteristics**





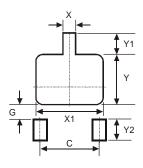


# Package Outline Dimensions



DFN2020B-3						
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A1	0	0.05	0.02			
А3	_	_	0.152			
b	0.20	0.30	0.25			
D	1.95	2.075	2.00			
D2	1.22	1.42	1.32			
D4	0.56	0.76	0.66			
е	_	_	0.65			
E	1.95	2.075	2.00			
E2	0.79	0.99	0.89			
E4	0.48	0.68	0.58			
L	0.25	0.35	0.30			
Z			0.225			
All D	All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
С	1.30
G	0.24
Х	0.35
X1	1.52
Y	1.09
Y1	0.47
Y2	0.50





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